

Vishay Siliconix

# Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	60
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.036
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.046
I <sub>D</sub> (A) per leg	8
Configuration	Dual

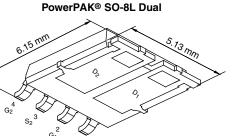
#### **FEATURES**

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified
- 100 % R<sub>q</sub> and UIS Tested
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

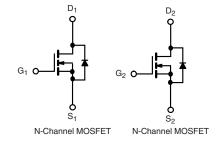




ROHS COMPLIANT HALOGEN FREE



**Bottom View** 



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ960EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_{\rm C}$	= 25 °C, unles	s otherwise noted	i)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	60		
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Dusin Currents	T <sub>C</sub> = 25 °C	1	8		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 125 °C	I <sub>D</sub>	8		
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	8	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	32		
Single Pulse Avalanche Current		I <sub>AS</sub>	16		
Single Pulse Avalanche Energy		E <sub>AS</sub>	12	mJ	
Maximum Dawar Dissinationh	T <sub>C</sub> = 25 °C	D	34	W	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	11		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>			260	·	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	85	°C // //	
Junction-to-Case (Drain)		$R_{thJC}$	4.3	°C/W	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static				l		ı	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> :	= 0 V, I <sub>D</sub> = 250 μA	60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	1
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	20	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.3 A	-	0.030	0.036	
Duain Caluras On State Resistance		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.3 A, T <sub>J</sub> = 125 °C	-	-	0.068	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.3 A, T <sub>J</sub> = 175 °C	-	-	0.084	Ω
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 4.5 A	-	0.040	0.046	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 5 A	-	16	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	587	735	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	114	145	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	]		-	49	65	
Total Gate Charge <sup>c</sup>	Qg			-	13	20	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_D = 4.5 \text{ A}$	-	1.6	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	3	-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	2	4	6	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	6	9	
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> :	= 30 V, $R_{\rm I}$ = 30 $\Omega$	-	8	12	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 1 \text{ A}, Y$	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	19	29	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			-	7	11	1
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	32	Α
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 5 A, V <sub>GS</sub> = 0 V		_	0.8	1.1	V

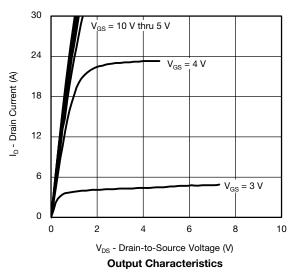
### Notes

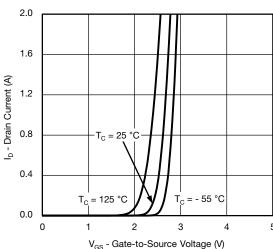
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

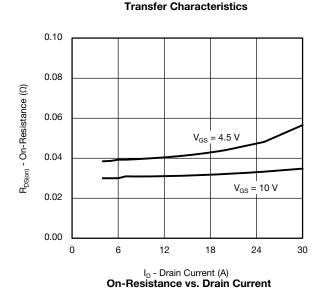
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

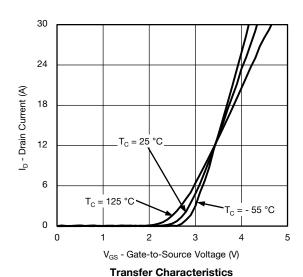


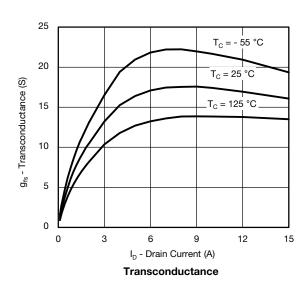
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

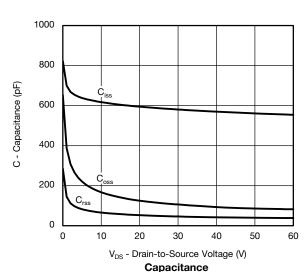






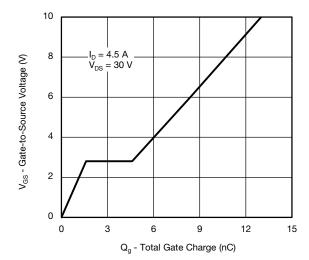




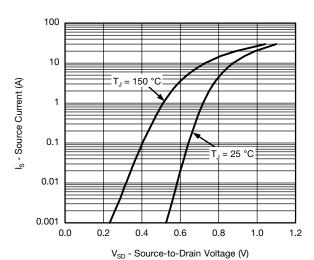




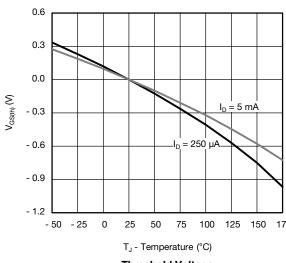
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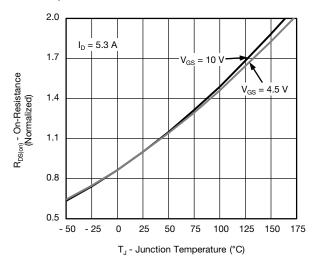
#### **Gate Charge**



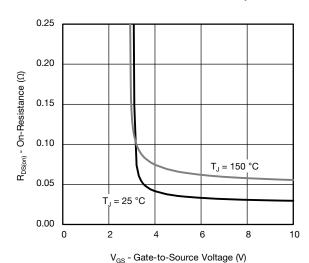
### Source Drain Diode Forward Voltage



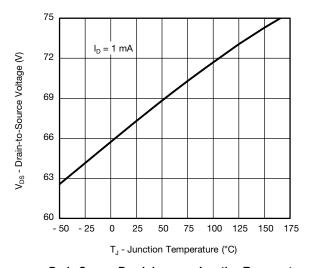
**Threshold Voltage** 



#### On-Resistance vs. Junction Temperature



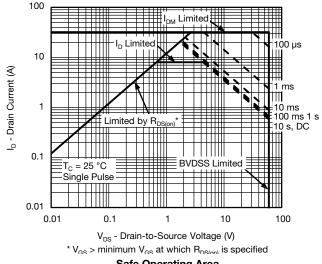




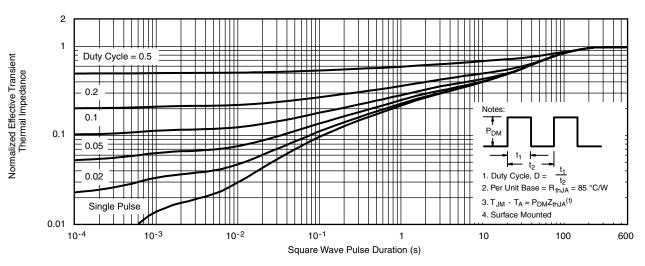
Drain Source Breakdown vs. Junction Temperature



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



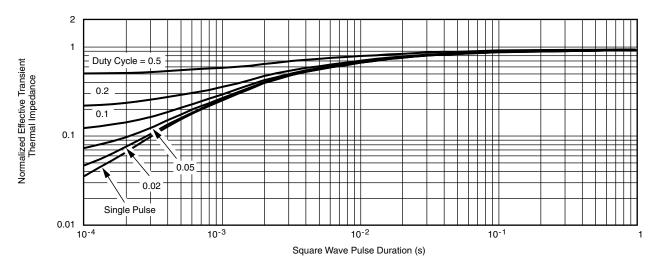




Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

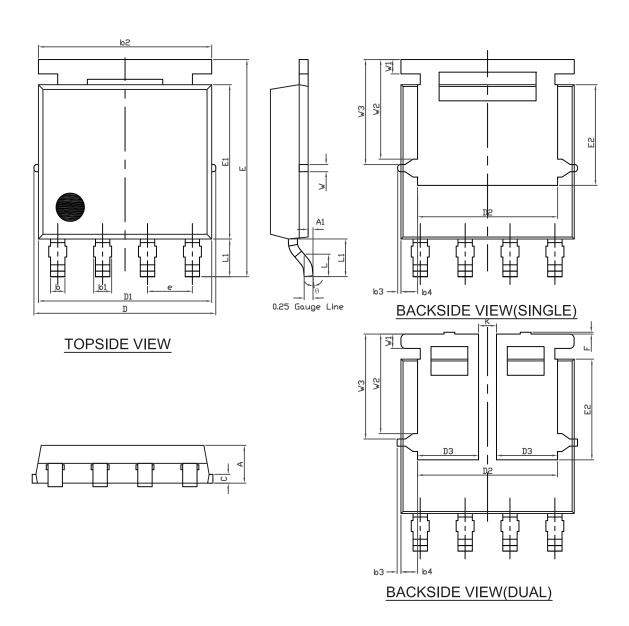
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267017">www.vishay.com/ppg267017</a>.

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# PowerPAK® SO-8L Case Outline



# **Package Information**

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DIM.		MILLIMETERS			INCHES	
DIWI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3		0.094			0.004	
b4		0.47			0.019	
С	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
е		1.27 BSC		0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2 (for Al product)	2.75	2.85	2.95	0.108	0.112	0.116
E2 (for other product)	3.18	3.28	3.38	0.125	0.129	0.133
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41		0.016			
W2	2.82		0.111			
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°

ECN: C12-0026-Rev. B, 27-Aug-12

DWG: 5976

#### Note

• Millimeters will gover



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